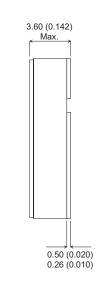




#### MECHANICAL DATA

Dimensions in mm (inches)

# (0.035)3.70 (0.146) min. 3.70 (0.146) 3.41 (0.134) 3.41 (0.134) 163) 151) 0.0 3 4.14 3.84 (0.421) 16.02 ( 15.73 ( 9.67 (0.381) 9.38 (0.369) 11.58 (0.456) 11.28 (0.444)



### P-CHANNEL **POWER MOSFET**

V<sub>DSS</sub> -100V I<sub>D(cont)</sub> -31A R<sub>DS(on)</sub>  $0.060\Omega$ 

### **FEATURES**

- HERMETICALLY SEALED SURFACE MOUNT PACKAGE
- SMALL FOOTPRINT EFFICIENT USE OF PCB SPACE.
- SIMPLE DRIVE REQUIREMENTS
- LIGHTWEIGHT
- HIGH PACKING DENSITIES

### SMD 1 PACKAGE (TO-276AB)

Pad 1 - Source

Pad 2 - Drain

Pad 3 - Gate

IRF5210SMD also available with pins 1 and 3 reversed.

## **ABSOLUTE MAXIMUM RATINGS** (T<sub>case</sub> = 25°C unless otherwise stated)

$V_{GS}$	Gate – Source Voltage	±20V		
I <sub>D</sub>	Continuous Drain Current $(V_{GS} = 0, T_{case} = 25^{\circ}C)$	-31A		
I <sub>D</sub>	Continuous Drain Current $(V_{GS} = 0, T_{case} = 100^{\circ}C)$	-19A		
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	-124A		
$P_{D}$	Power Dissipation @ T <sub>case</sub> = 25°C	125W		
	Linear Derating Factor	1.0W/°C		
E <sub>AS</sub>	Single Pulse Avalanche Energy <sup>2</sup>	340mJ		
dv/dt	Peak Diode Recovery <sup>3</sup>	4.0V/ns		
$T_J$ , $T_stg$	Operating and Storage Temperature Range	−55 to 150°C		
TL	Package Mounting Surface Temperature (for 5 sec)	300°C		
$R_{\theta JC}$	Thermal Resistance Junction to Case	1.0°C/W		

**Notes** 1) Pulse Test: Pulse Width  $\leq$  300ms,  $\delta \leq$  2%

2) @  $V_{DD}$  = -25V , L = 1.9mH , Peak  $I_{AS}$  = -19A ,  $V_{GS}$  = -10V,  $R_{G}$  = 25 $\Omega$ , Starting  $T_{J}$  = 25°C

3) @  $I_{SD} \le -19A$ , di/dt  $\le -390A/\mu s$ ,  $V_{DD} \le -100V$ ,  $T_J \le 150^{\circ} C$ 

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

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# **ELECTRICAL CHARACTERISTICS** (T<sub>amb</sub> = 25°C unless otherwise stated)

	Parameter	Test Cond	litions	Min.	Тур.	Max.	Unit			
	STATIC ELECTRICAL RATINGS									
BV <sub>DSS</sub>	Drain – Source Breakdown Voltage	V <sub>GS</sub> = 0	I <sub>D</sub> = -250μA	-100			V			
$\Delta BV_{DSS}$	Temperature Coefficient of	Reference to 25°C			-0.11		V/°C			
$\Delta T_{J}$	Breakdown Voltage	$I_D = -1 \text{mA}$			-0.11					
R <sub>DS(on)</sub>	Static Drain – Source On–State Resistance <sup>1</sup>	V <sub>GS</sub> = -10V	I <sub>D</sub> = -19A			0.06	Ω			
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}$	$I_D = -250 \mu A$	-2.0		-4.0	V			
9 <sub>fs</sub>	Forward Transconductance <sup>1</sup>	V <sub>DS</sub> = -50V	I <sub>DS</sub> = -19A	10			S(Ω)			
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>GS</sub> = 0	V <sub>DS</sub> = -80V T <sub>.I</sub> = 125°C			-25 -250	μА			
I <sub>GSS</sub>	Forward Gate – Source Leakage	V <sub>GS</sub> = -20V	-			-100				
I <sub>GSS</sub>	Reverse Gate – Source Leakage	V <sub>GS</sub> = 20V				100	⊢ nA			
300	DYNAMIC CHARACTERISTICS									
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0			2700					
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = -25V		830		pF				
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1MHz			470					
Qg	Total Gate Charge <sup>1</sup>	$V_{GS} = -10V$ $V_{DS} = -80V$	I <sub>D</sub> = -19A			215	nC			
Q <sub>gs</sub>	Gate – Source Charge <sup>1</sup>	V <sub>GS</sub> = -10V	I <sub>D</sub> = -19A			30	-0			
Q <sub>gd</sub>	Gate - Drain ("Miller") Charge 1	$V_{DS} = -80V$				115	nC			
t <sub>d(on)</sub>	Turn-On Delay Time		V <sub>GS</sub> = -10V			28	ns			
t <sub>r</sub>	Rise Time	$V_{DD} = -50V$				150				
t <sub>d(off)</sub>	Turn-Off Delay Time	$I_D = -19A$ $R_G = 2.5\Omega$				103				
t <sub>f</sub>	Fall Time					116				
	SOURCE - DRAIN DIODE CHARAC	TERISTICS		-1						
I <sub>S</sub>	Continuous Source Current					-31	٨			
I <sub>SM</sub>	Pulse Source Current <sup>2</sup>					-124	<b> </b>			
V <sub>SD</sub>	Diode Forward Voltage	$I_S = -19A$ $V_{GS} = 0$	T <sub>J</sub> = 25°C			-1.6	V			
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = -19A	$T_J = 25^{\circ}C$			290	ns			
Q <sub>rr</sub>	Reverse Recovery Charge	$d_i / d_t \le 100A/\mu$	is $V_{DD} \le -50V$			2.1	μС			
t <sub>on</sub>	Forward Turn-On Time			Negligible						

### **Notes**

- 1) Pulse Test: Pulse Width  $\leq$  300ms,  $\delta \leq$  2%
- 2) Repetitive Rating Pulse width limited by maximum junction temperature.

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